onsemi

Operational Amplifier, Precision, Zero-Drift, 50 μV Offset, 0.25 μV/°C, 35 μA

NCS325, NCS2325, NCS4325

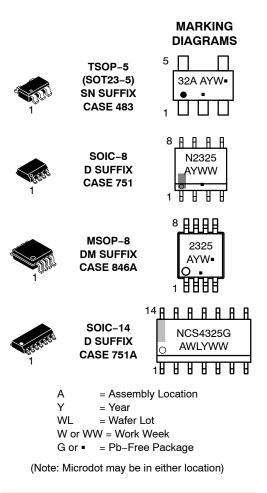
The NCS325, NCS2325 and NCS4325 are CMOS operational amplifiers providing precision performance. The Zero–Drift architecture allows for continuous auto–calibration, which provides very low offset, near–zero drift over time and temperature, and near flat 1/f noise at only 35 μ A (max) quiescent current. These benefits make these devices ideal for precision DC applications. These op amps provide rail–to–rail input and output performance and are optimized for low voltage operation as low as 1.8 V and up to 5.5 V. The single channel NCS325 is available in the space–saving SOT23–5 package. The dual channel NCS4325 is available in Micro8 and SOIC–8. The quad channel NCS4325 is available in SOIC–14.

Features

- Low Offset Voltage: 14 μV typ, 50 μV max at 25°C for NCS325
- Zero Drift: 0.25 μ V/°C max
- Low Noise: 1 µVpp, 0.1 Hz to 10 Hz
- Quiescent Current: 21 µA typ, 35 µA max at 25°C
- Supply Voltage: 1.8 V to 5.5 V
- Rail-to-Rail Input and Output
- Internal EMI Filtering
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

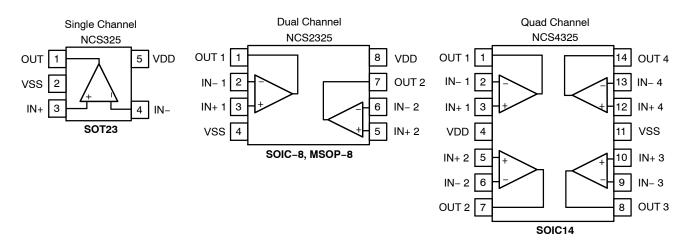
- Battery Powered Instruments
- Temperature Measurements
- Transducer Applications
- Electronic Scales
- Medical Instrumentation
- Current Sensing



ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

PIN CONNECTIONS



ORDERING INFORMATION

Configuration	Device	Package	Shipping [†]
Single	NCS325SN2T1G	SOT23-5 / TSOP-5	3000 / Tape & Reel
Dual	NCS2325DR2G	SOIC-8	3000 / Tape & Reel
	NCS2325DMR2G	Micro8 / MSOP-8	4000 / Tape & Reel
Quad	NCS4325DR2G	SOIC-14	2500 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, <u>BRD8011/D</u>.

ABSOLUTE MAXIMUM RATINGS Over operating free-air temperature, unless otherwise stated.

Parameter	Rating	Unit
Supply Voltage	6	V
INPUT AND OUTPUT PINS		
Input Voltage (Note 1)	(V _{SS}) – 0.3 to (V _{DD}) + 0.3	V
Input Current (Note 1)	±10	mA
Output Short Circuit Current (Note 2)	Continuous	
TEMPERATURE		
Operating Temperature	-40 to +150	°C
Storage Temperature	-65 to +150	°C
Junction Temperature	+150	°C
ESD RATINGS (Note 3)		-
Human Body Model (HBM)	4000	V
Machine Model (MM)	200	V
OTHER RATINGS		•
		1

Latch-up Current (Note 4)	100	mA
MSL	Level 1	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Input terminals are diode-clamped to the power-supply rails. Input signals that can swing more than 0.3 V beyond the supply rails should be current limited to 10 mA or less

2. Short-circuit to ground.

 This device series incorporates ESD protection and is tested by the following methods: ESD Human Body Model tested per AEC-Q100-002 (JEDEC standard: JESD22-A114) ESD Machine Model tested per AEC-Q100-003 (JEDEC standard: JESD22-A115)

4. Latch-up Current tested per JEDEC standard: JESD78.

THERMAL INFORMATION

Thermal Metric	Symbol	Package	Value	Unit
Junction to Ambient (Note 5)	θ_{JA}	SOT23-5 / TSOP-5	235	°C/W
		Micro8 / MSOP-8	298	
		SOIC-8	250	
		SOIC-14	216	

5. As mounted on an 80x80x1.5 mm FR4 PCB with 650 mm² and 2 oz (0.034 mm) thick copper heat spreader. Following JEDEC JESD/EIA 51.1, 51.2, 51.3 test guidelines

OPERATING CONDITIONS

Parameter	Symbol	Range	Unit
Supply Voltage (V _{DD} – V _{SS})	V _S	1.8 to 5.5	V
Specified Operating Range	T _A	-40 to 125	°C
Input Common Mode Voltage Range	VICMR	V_{SS} –0.1 to V_{DD} +0.1	V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

ELECTRICAL CHARACTERISTICS: $V_S = 1.8 \text{ V to } 5.5 \text{ V}$ At $T_A = +25^{\circ}\text{C}$, $R_L = 10 \text{ k}\Omega$ connected to midsupply, $V_{CM} = V_{OUT} = \text{midsupply}$, unless otherwise noted.

Boldface	limits apply over	the specified temperature range	ge, T _A = -40°C to 125°C	C, guaranteed by characterization and/or design.

Parameter	Symbol		Conditions	Min	Тур	Max	Unit
INPUT CHARACTERISTICS							
Offset Voltage	V _{OS}	NCS325	V _S = +5V		14	50	μV
		NCS2325, NCS4325	$V_S = +5V$		14	75	
Offset Voltage Drift vs Temp	$\Delta V_{OS} / \Delta T$		T _A = −40°C to 125°C		0.02	0.25	μV/°C
Input Bias Current	I _{IB}				±50		pА
Input Offset Current	I _{OS}				±100		pА
Common Mode Rejection Ratio	CMRR	NCS325	V_{SS} +0.3 < V_{CM} < V_{DD} - 0.3, V_{S} = 1.8 V	85	108		dB
			V_{SS} +0.3 < V_{CM} < V_{DD} - 0.3, V_{S} = 5.5 V	90	110		
		NCS2325, NCS4325	V_{SS} +0.3 < V_{CM} < V_{DD} – 0.3, V_{S} = 5 V	90	110		
		V_{SS} -0.1 < V_{CM} < V_{DD} + 0.1, V_{S} = 1.8 V			80		
		V _{SS} -0.1 <	$< V_{CM} < V_{DD} + 0.1, V_{S} = 5.5 V$		92		
Input Resistance	R _{IN}				15		GΩ
Input Capacitance	C _{IN}	NCS325	Differential		1.8		pF
			Common Mode		3.5		pF
		NCS2325,	Differential		4.1		pF
		NCS4325	Common Mode		8.0		pF
OUTPUT CHARACTERISTICS							
Output Voltage High	V _{OH}	0	utput swing within V _{DD}		12	100	mV
Output Voltage Low	V _{OL}	0	utput swing within V _{SS}		8	100	mV
Short Circuit Current	I _{SC}				±5		mA

Short Circuit Current	I _{SC}			±5		mA
Open Loop Output Impedance	Z _{out-OL}	f = 350 kHz, I_0 = 0 mA, V_S = 1.8 V		1.4		kΩ
		f = 350 kHz, I _O = 0 mA, V _S = 5.5 V		2.7		
Capacitive Load Drive	CL		ę	See Figure)	

NOISE PERFORMANCE

Voltage Noise Density	e _N	f _{IN} = 1 kHz	100	nV / √ Hz
Voltage Noise	e _{P-P}	f _{IN} = 0.01 Hz to 1 Hz	0.3	μV_{PP}
		f _{IN} = 0.1 Hz to 10 Hz	1	μV_{PP}
Current Noise Density	i _N	f _{IN} = 10 Hz	0.3	pA / √ Hz

DYNAMIC PERFORMANCE

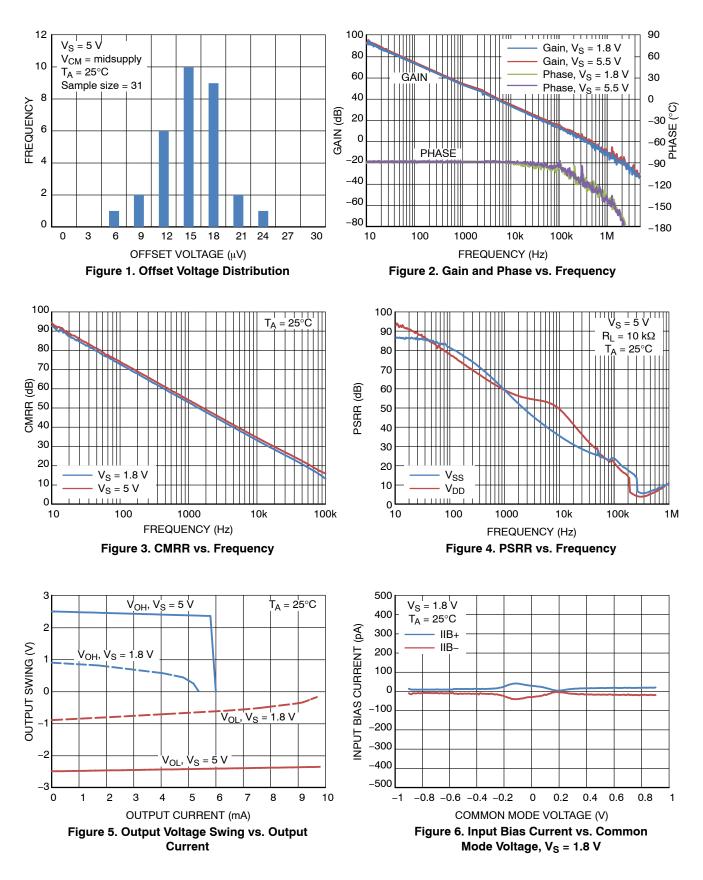
Open Loop Voltage Gain	A _{VOL}	R_L = 10 k Ω , V_S = 5.5 V		114	dB
Gain Bandwidth Product	GBWP	NCS325	C_L = 100 pF, R_L = 10 k Ω	350	kHz
		NCS2325, NCS4325	C_L = 100 pF, R_L = 10 k Ω	270	
Phase Margin	ϕ_{M}	C _L = 100 pF		60	0
Gain Margin	A _M	C _L = 100 pF		20	dB
Slew Rate	SR	G = +1, C _L = 100 pF, Vs = 1.8 V		0.10	V/μs
		G = +	1, C _L = 100 pF, Vs = 5.5 V	0.16	

POWER SUPPLY

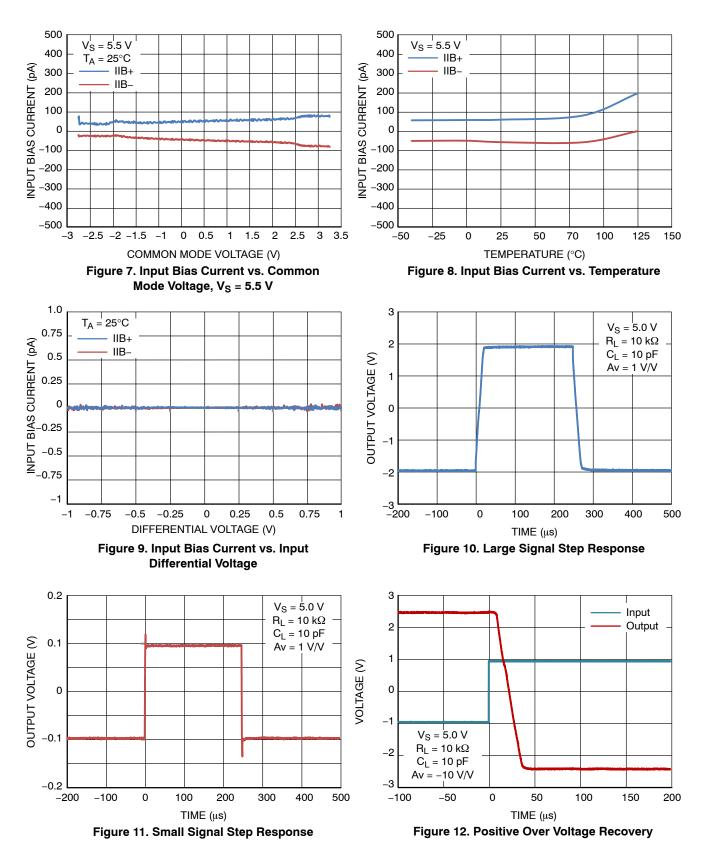
Power Supply Rejection Ratio	PSRR		100	107		dB
		$T_A = -40^{\circ}C$ to $125^{\circ}C$	95			
Turn-on Time	t _{ON}	V _S = 5 V		100		μs
Quiescent Current	Ι _Q	No load		21	35	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

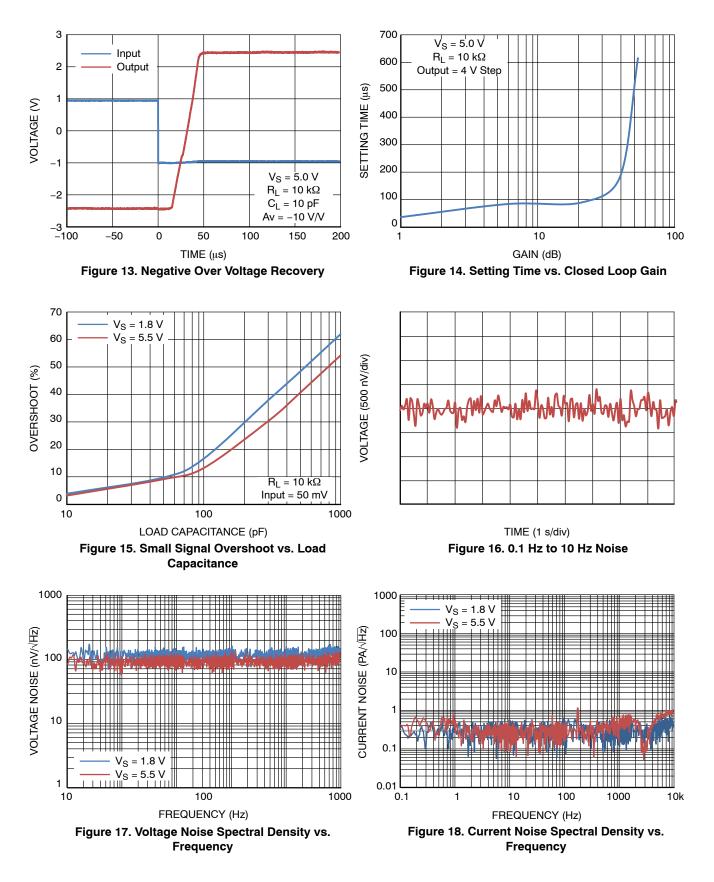
TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS (Continued)



TYPICAL CHARACTERISTICS (Continued)



TYPICAL CHARACTERISTICS (Continued)

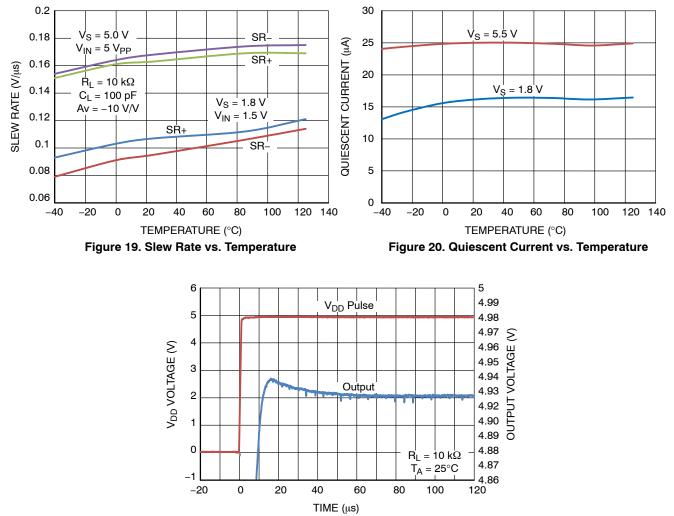


Figure 21. Turn-on Response

APPLICATIONS INFORMATION

INPUT VOLTAGE

The NCS325, NCS2325 and NCS4325 have rail-to-rail common mode input voltage range. Diodes between the inputs and the supply rails keep the input voltage from exceeding the rails.

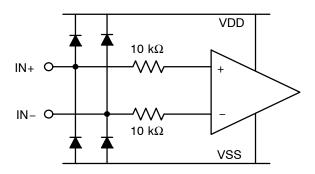


Figure 22. Equivalent Input Circuit

EMI SUSCEPTIBILITY AND INPUT FILTERING

Op amps have varying amounts of EMI susceptibility. Semiconductor junctions can pick up and rectify EMI signals, creating an EMI-induced voltage offset at the output, adding another component to the total error. Input pins are the most sensitive to EMI. The NCS325, NCS2325 and NCS4325 integrate a low-pass filter to decrease its sensitivity to EMI.

APPLICATION CIRCUITS

Low-Side Current Sensing

The goal of low-side current sensing is to detect over-current conditions or as a method of feedback control. A sense resistor is placed in series with the load to ground. Typically, the value of the sense resistor is less than 100 m Ω to reduce power loss across the resistor. The op amp amplifies the voltage drop across the sense resistor with a gain set by external resistors R1, R2, R3, and R4 (where R1 = R2, R3 = R4). Precision resistors are required for high accuracy, and the gain is set to utilize the full scale of the ADC for the highest resolution.

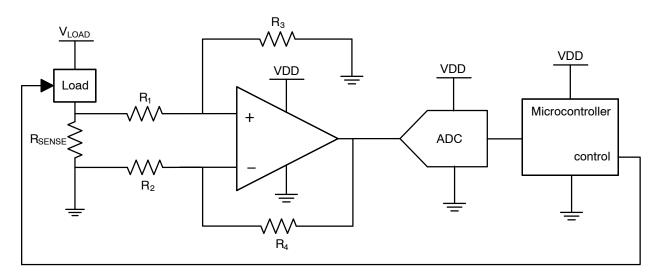


Figure 23. Low-Side Current Sensing

Differential Amplifier for Bridged Circuits

Sensors to measure strain, pressure, and temperature are often configured in a Wheatstone bridge circuit as shown in Figure 24. In the measurement, the voltage change that is produced is relatively small and needs to be amplified before going into an ADC. Precision amplifiers are recommended in these types of applications due to their high gain, low noise, and low offset voltage.

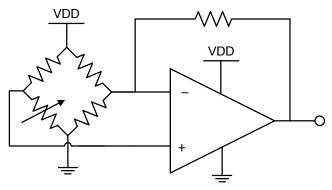


Figure 24. Bridge Circuit Amplification

GENERAL LAYOUT GUIDELINES

To ensure optimum device performance, it is important to follow good PCB design practices. Place $0.1 \,\mu\text{F}$ decoupling capacitors as close as possible to the supply pins. Keep traces short, utilize a ground plane, choose surface-mount components, and place components as close as possible to

the device pins. These techniques will reduce susceptibility to electromagnetic interference (EMI). Thermoelectric effects can create an additional temperature dependent offset voltage at the input pins. To reduce these effects, use metals with low thermoelectric-coefficients and prevent temperature gradients from heat sources or cooling fans.





DOCUMENT NUMBER:	98ARB18753C	Electronic versions are uncontrolled except when accessed directly from the Document Repository Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.					
DESCRIPTION:	TSOP-5	PAGE 1					
ON Semiconductor reserves the right the suitability of its products for any pa	ON Semiconductor and a re trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the						

onsemí



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42564B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOIC-8 NB		PAGE 1 OF 2
onsemi and ONSEMi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.			

SOIC-8 NB CASE 751-07 **ISSUE AK**

STYLE 1: PIN 1. EMITTER COLLECTOR 2. 3. COLLECTOR 4. EMITTER 5. EMITTER BASE 6. 7 BASE EMITTER 8. STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN DRAIN 4. GATE 5. 6. GATE SOURCE 7. 8. SOURCE STYLE 9: PIN 1. EMITTER, COMMON COLLECTOR, DIE #1 COLLECTOR, DIE #2 2. З. EMITTER, COMMON 4. 5. EMITTER, COMMON 6 BASE. DIE #2 BASE, DIE #1 7. 8. EMITTER, COMMON STYLE 13: PIN 1. N.C. 2. SOURCE 3 GATE 4. 5. DRAIN 6. DRAIN DRAIN 7. DRAIN 8. STYLE 17: PIN 1. VCC 2. V2OUT V10UT З. TXE 4. 5. RXE 6. VFF 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3 CATHODE 3 CATHODE 4 4. 5. CATHODE 5 6. COMMON ANODE COMMON ANODE 7. 8. CATHODE 6 STYLE 25: PIN 1. VIN 2 N/C REXT З. 4. GND 5. IOUT IOUT 6. IOUT 7. 8. IOUT STYLE 29: BASE, DIE #1 PIN 1. 2 EMITTER, #1 BASE, #2 З. EMITTER, #2 4. 5 COLLECTOR, #2 COLLECTOR, #2 6.

STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 COLLECTOR, #2 3. 4 COLLECTOR, #2 BASE, #2 5. EMITTER, #2 6. 7 BASE #1 EMITTER, #1 8. STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN SOURCE 4. SOURCE 5. 6. GATE GATE 7. 8. SOURCE STYLE 10: GROUND PIN 1. BIAS 1 OUTPUT 2. З. GROUND 4. 5. GROUND 6 BIAS 2 INPUT 7. 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3 P-SOURCE P-GATE 4. P-DRAIN 5 6. P-DRAIN N-DRAIN 7. N-DRAIN 8. STYLE 18: PIN 1. ANODE ANODE 2. SOURCE 3. GATE 4. 5. DRAIN 6 DRAIN CATHODE 7. CATHODE 8. STYLE 22 PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3 COMMON CATHODE/VCC 4. I/O LINE 3 COMMON ANODE/GND 5. 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND STYLE 26: PIN 1. GND 2 dv/dt З. ENABLE 4. ILIMIT 5. SOURCE SOURCE 6. SOURCE 7. 8. VCC STYLE 30: DRAIN 1 PIN 1. DRAIN 1 2 GATE 2 З. SOURCE 2 4 SOURCE 1/DRAIN 2 SOURCE 1/DRAIN 2 5.

6.

7.

8 GATE 1

SOURCE 1/DRAIN 2

STYLE 3: PIN 1. DRAIN, DIE #1 DRAIN, #1 2. DRAIN, #2 З. DRAIN, #2 4. GATE, #2 5. SOURCE, #2 6. 7 GATE #1 8. SOURCE, #1 STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS THIRD STAGE SOURCE GROUND З. 4. 5. DRAIN 6. GATE 3 SECOND STAGE Vd 7. FIRST STAGE Vd 8. STYLE 11: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. З. GATE 2 4. 5. DRAIN 2 6. DRAIN 2 DRAIN 1 7. 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 ANODE 1 3 ANODE 1 4. 5. CATHODE, COMMON CATHODE, COMMON CATHODE, COMMON 6. 7. CATHODE, COMMON 8. STYLE 19: PIN 1. SOURCE 1 GATE 1 SOURCE 2 2. 3. GATE 2 4. 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 MIRROR 1 8. STYLE 23: PIN 1. LINE 1 IN COMMON ANODE/GND COMMON ANODE/GND 2. 3 LINE 2 IN 4. LINE 2 OUT 5. COMMON ANODE/GND COMMON ANODE/GND 6. 7. 8. LINE 1 OUT STYLE 27: PIN 1. ILIMIT OVI O 2 UVLO З. 4. INPUT+ 5. 6. SOURCE SOURCE SOURCE 7. 8 DRAIN

DATE 16 FEB 2011

STYLE 4: PIN 1. 2. ANODE ANODE ANODE З. 4. ANODE ANODE 5. 6. ANODE 7 ANODE COMMON CATHODE 8. STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 З. BASE #2 COLLECTOR, #2 4. COLLECTOR, #2 5. 6. EMITTER, #2 EMITTER, #1 7. 8. COLLECTOR, #1 STYLE 12: PIN 1. SOURCE SOURCE 2. 3. GATE 4. 5. DRAIN 6 DRAIN DRAIN 7. 8. DRAIN STYLE 16 EMITTER, DIE #1 PIN 1. 2. BASE, DIE #1 EMITTER, DIE #2 3 BASE, DIE #2 4. 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 COLLECTOR, DIE #1 7. COLLECTOR, DIE #1 8. STYLE 20: PIN 1. SOURCE (N) GATE (N) SOURCE (P) 2. 3. 4. GATE (P) 5. DRAIN 6. DRAIN DRAIN 7. 8. DRAIN STYLE 24: PIN 1. BASE EMITTER 2. 3 COLLECTOR/ANODE COLLECTOR/ANODE 4. 5. CATHODE 6. CATHODE COLLECTOR/ANODE 7. 8. COLLECTOR/ANODE STYLE 28: PIN 1. SW_TO_GND 2. DASIC OFF DASIC_SW_DET З. 4. GND 5. 6. V MON VBULK 7. VBULK 8 VIN

DOCUMENT NUMBER:	98ASB42564B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOIC-8 NB F		PAGE 2 OF 2

onsem and of isor in are trademarks or semiconductor compension instructions, the do onsem or its subsidiaries in the oniced states and/or outrofts, or non-emitting the subsidiaries in the oniced states and/or outrofts, or non-emitting the subsidiaries in the oniced states and/or outrofts, or non-emitting the subsidiaries in the oniced states and/or outrofts, or non-emitting the subsidiaries in the oniced states and/or outrofts, or non-emitting the subsidiaries in the oniced states and/or outrofts, or non-emitting the subsidiaries in the oniced states and/or outrofts, or non-emitting the subsidiaries in the oniced states and/or outrofts, or non-emitting the subsidiaries in the oniced states and/or outrofts, or non-emitting the subsidiaries in the oniced states and/or outrofts, or non-emitting the subsidiaries in the oniced states and/or outrofts, or non-emitting the subsidiaries in the oniced states and/or outrofts, or non-emitting the subsidiaries in the oniced states and/or outrofts, or non-emitting the subsidiaries in the oniced states and/or outrofts, or non-emitting the subsidiaries in the oniced states and/or outrofts, or non-emitting the subsidiaries in the oniced states and/or outrofts, or non-emitting the subsidiaries in the oniced states and/or outrofts, or non-emitting the subsidiaries in the oniced states and/or outrofts, or non-emitting the subsidiaries in the oniced states and/or outrofts, or non-emitting the subsidiaries in the oniced states and/or outrofts, or non-emitting the subsidiaries in the oniced states and/or outrofts, or non-emitting the subsidiaries in the oniced states and/or outrofts, or non-emitting the subsidiaries in the oniced states and/or outrofts, or non-emitting the subsidiaries in the oniced states and/or outrofts, or non-emitting the subsidiaries in the oniced states and/or outrofts, or non-emitting the subsidiaries in the oniced states and/or outrofts, or non-emitting the subsidiaries in the oniced states and/or outrofts, or non-emitting the subsidiaries in the oniced stat purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

7.

8

COLLECTOR, #1

COLLECTOR, #1

DUSEM

0.068

0.019

0.344

0.244



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

Electronic versions are uncontrolled except when accessed directly from the Document Repository. DOCUMENT NUMBER: 98ASB42565B Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. **DESCRIPTION:** SOIC-14 NB PAGE 1 OF 2 onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

SOIC-14 CASE 751A-03 ISSUE L

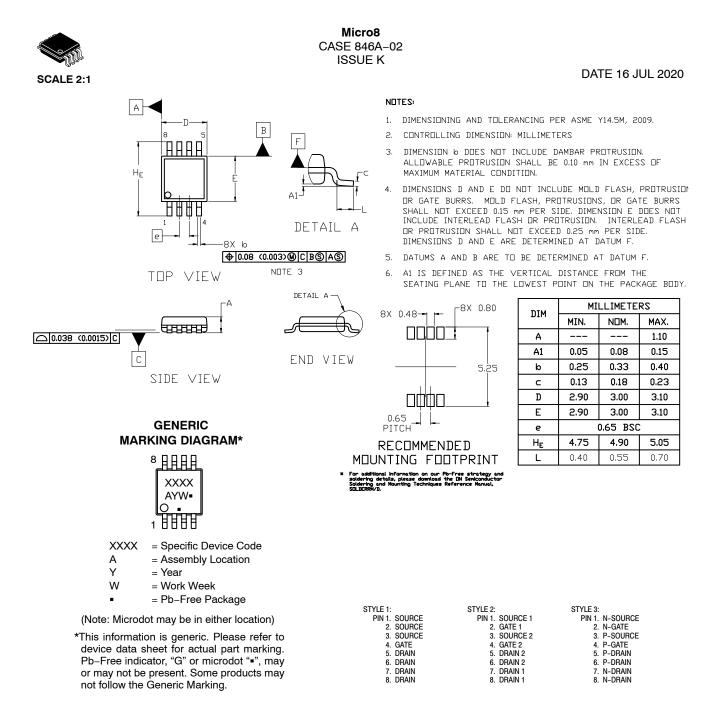
DATE 03 FEB 2016

STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 2: CANCELLED	STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON CATHODE 13. ANODE/CATHODE 14. ANODE/CATHODE	STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE

DOCUMENT NUMBER:	98ASB42565B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOIC-14 NB		PAGE 2 OF 2

onsemi and ONSEMI: are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.





DOCUMENT NUMBER:	98ASB14087C	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	MICRO8		PAGE 1 OF 1
ON Semiconductor and I are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the			

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and calcular performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

TECHNICAL SUPPORT

onsemi Website: www.onsemi.com

Email Requests to: orderlit@onsemi.com

North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support: Phone: 00421 33 790 2910 For additional information, please contact your local Sales Representative

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

onsemi:

NCS325SN2T1G NCS2325DMR2G NCS4325DR2G NCS2325DR2G